

Low Voltage Quad 2-Input NAND Schmitt Trigger

74LVX132

General Description

The LVX132 contains four 2-input NAND Schmitt Trigger Gates. The pin configuration and function are the same as the LVX00 but the inputs have hysteresis between the positive-going and negative-going input thresholds, which are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals, thus providing greater noise margins than conventional gates.

The inputs tolerate voltages up to 6.5~V allowing the interface of 5~V systems to 3~V systems.

Features

- Input Voltage Level Translation from 5 V to 3 V
- Ideal for Low Power/Low Noise 3.3 V Applications
- Guaranteed Simultaneous Switching Noise Level and Dynamic Threshold Performance
- Pb-Free, Halogen Free/BFR Free and RoHS Compliant

Logic Diagram

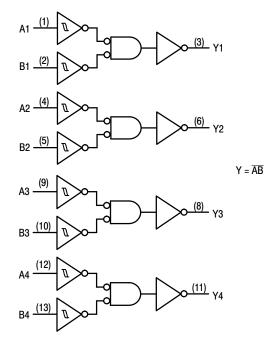


Figure 1. Logic Diagram



MARKING DIAGRAM

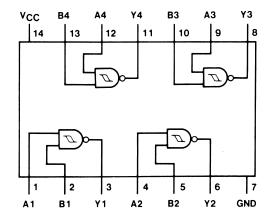


XXXXX = Specific Device Code A = Assembly Location

L = Wafer Lot Y = Year W = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

CONNECTION DIAGRAM



PIN DESCRIPTION

Pin Names	Description
A _n , B _n	Inputs
Y _n	Outputs

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +6.5	V
I _{IK}	DC Input Diode Current, V _I = -0.5 V	-20	mA
V _I	DC Input Voltage	-0.5 to +6.5	V
I _{OK}	DC Output Diode Current $V_{O} = -0.5 \text{ V}$ $V_{O} = V_{CC} + 0.5 \text{ V}$	-20 +20	mA
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
Ι _Ο	DC Output Source or Sink Current	±25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	±50	mA
T _{STG}	Storage Temperature	-65 to +150	°C
P_{D}	Power Dissipation	833	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS (Note 1)

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	2.0	3.6	V
VI	Input Voltage	0	5.5	V
Vo	Output Voltage	0	V _{CC}	V
T _A	Operating Temperature	-40	+85	°C
Δt / ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. Unused inputs must be held HIGH or LOW. They may not float.

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DC ELECTRICAL CHARACTERISTICS

						T _A = 25°C		T _A = -40°0	C to +85°C	
Symbol	Parameter	V _{CC} (V)	Con	ditions	Min	Тур	Max	Min	Max	Unit
V _{t+}	Positive Threshold	3.0			-	-	2.2	-	2.2	V
V_{t-}	Negative Threshold	3.0			0.9	_	-	0.9	-	V
V _H	Hysteresis	3.0			0.3	-	1.2	0.3	1.2	V
V _{OH}	HIGH Level Output	2.0	$V_{IN} = V_{IL}$	I _{OH} = -50 μA	1.9	2.0	-	1.9	-	V
	Voltage	3.0	or V _{IH}	I _{OH} = -50 μA	2.9	3.0	-	2.9	-	
		3.0		I _{OH} = -4 mA	2.58	-	-	2.48	-	
V _{OL}	LOW Level Output	2.0	$V_{IN} = V_{IL}$	I _{OL} = 50 μA	-	0.0	0.1	-	0.1	V
	Voltage	3.0	or V _{IH}	I _{OL} = 50 μA	-	0.0	0.1	-	0.1	
		3.0		I _{OL} = 4 mA	-	_	0.36	-	0.44	
I _{IN}	Input Leakage Current	3.6	V _{IN} = 5.5 V or GND		-	-	±0.1	-	±1.0	μА
Icc	Quiescent Supply Current	3.6	V _{IN} = V _{CC} or	GND	-	-	2.0	-	20.0	μΑ

NOISE CHARACTERISTICS (Note 2)

				T _A = 25°C		
Symbol	Parameter	V _{CC} (V)	Conditions	Тур	Limit	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3	C _L = 50 pF	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3	C _L = 50 pF	-0.3	-0.5	V
V _{IHD}	Minimum HIGH Level Dynamic Input Voltage	3.3	C _L = 50 pF	-	2.0	V
V_{ILD}	Maximum LOW Level Dynamic Input Voltage	3.3	C _L = 50 pF	-	0.8	V

^{2.} Input $t_r = t_f = 3 \text{ ns}$

AC ELECTRICAL CHARACTERISTICS

				T _A = 25°C		T _A = -40°C			
Symbol	Parameter	V _{CC} (V)	Conditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay Time	2.7	C _L = 15 pF	-	7.0	11.5	1.0	13.0	ns
	Tille	•	C _L = 50 pF	-	10.5	16.0	1.0	18.7	
		3.3 ±0.3	C _L = 15 pF	-	6.1	10.6	1.0	12.5	ns
		•	C _L = 50 pF	-	9.0	15.4	1.0	17.5	
t _{OSLH} ,	Output to Output	2.7	C _L = 50 pF	-	-	1.5	-	1.5	ns
toshl	Skew (Note 3)	3.3		-	-	1.5	-	1.5	

^{3.} Parameter guaranteed by design $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$

CAPACITANCE

			T _A = 25°C		T _A = -40°C to +85°C			
Symbol	Parameter	Conditions	Min	Тур	Max	Min	Max	Unit
C _{IN}	Input Capacitance		-	4	10	-	10	pF
C _{PD}	Power Dissipation Capacitance (Note 4)		-	18	-	-	-	pF

^{4.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(opr.)} = (C_{PD} \times V_{CC} \times f_{IN} \times I_{CC}) / 6 \text{ (per Gate)}$

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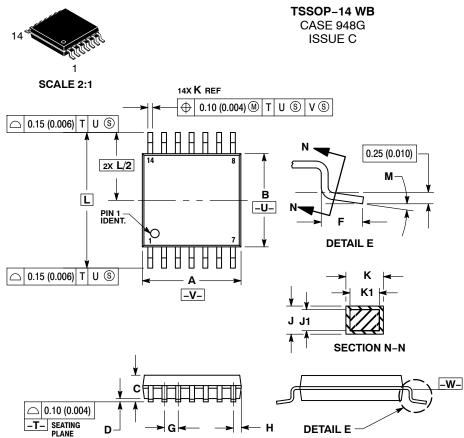
ORDERING INFORMATION

Device Order Number	Top Marking	Package Type	Shipping [†]
74LVX132MTCX	LVX 132	TSSOP-14 WB (Pb-Free, Halide Free)	2500 units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DATE 17 FEB 2016





- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0 °	8 °	0 °	8 °	

GENERIC MARKING DIAGRAM*



= Assembly Location

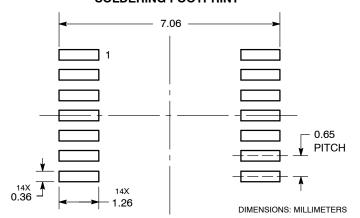
= Wafer Lot L = Year = Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	TSSOP-14 WB		PAGE 1 OF 1		

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